Sergey V Balakirev

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/8410035/publications.pdf

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20 200 9 14
papers citations h-index g-index

20 20 20 41

times ranked

citing authors

docs citations

all docs

| # | Article | IF | CITATIONS |
|----|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----------|
| 1 | Hybrid Analytical–Monte Carlo Model of In/GaAs(001) Droplet Epitaxy: Theory and Experiment. Physica Status Solidi (B): Basic Research, 2018, 255, 1700360. | 1.5 | 25 |
| 2 | Study of Nanoscale Profiling Modes of GaAs Epitaxial Structures by Focused Ion Beams. Nanotechnologies in Russia, 2018, 13, 26-33. | 0.7 | 21 |
| 3 | Mechanism of nucleation and critical layer formation during In/GaAs droplet epitaxy. Nanotechnology, 2019, 30, 505601. | 2.6 | 21 |
| 4 | Monte Carlo simulation of the kinetic effects on GaAs/GaAs(001) MBE growth. Journal of Crystal Growth, 2017, 457, 46-51. | 1.5 | 20 |
| 5 | Effect of interaction in the Ga–As–O system on the morphology of a GaAs surface during molecular-beam epitaxy. Physics of the Solid State, 2016, 58, 1045-1052. | 0.6 | 18 |
| 6 | Monte Carlo investigation of the influence of V/III flux ratio on GaAs/GaAs(001) submonolayer epitaxy. Technical Physics, 2016, 61, 971-977. | 0.7 | 16 |
| 7 | Monte Carlo simulation of V/III flux ratio influence on GaAs island nucleation during MBE. Journal of Physics: Conference Series, 2016, 681, 012036. | 0.4 | 15 |
| 8 | Kinetic Monte Carlo simulation of GaAs(001) MBE growth considering the V/III flux ratio effect. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, 041804. | 1.2 | 15 |
| 9 | Droplet epitaxy of GaAs nanostructures on the As-stabilized GaAs(001) surface. Journal of Physics: Conference Series, 2017, 917, 032037. | 0.4 | 12 |
| 10 | Anomalous behavior of In adatoms during droplet epitaxy on the AlGaAs surfaces. Nanotechnology, 2020, 31, 485604. | 2.6 | 9 |
| 11 | Independent Control Over Size and Surface Density of Droplet Epitaxial Nanostructures Using Ultra-Low Arsenic Fluxes. Nanomaterials, 2021, 11, 1184. | 4.1 | 8 |
| 12 | Effect of GaAs native oxide upon the surface morphology during GaAs MBE growth. Journal of Physics: Conference Series, 2016, 741, 012012. | 0.4 | 5 |
| 13 | MBE formation of self-catalyzed GaAs nanowires using ZnO nanosized films. Journal of Physics: Conference Series, 2018, 1124, 081024. | 0.4 | 4 |
| 14 | Low-density arrays of ultra-small InAs nanostructures obtained by two-stage arsenic exposure during droplet epitaxy. Applied Surface Science, 2022, 578, 152023. | 6.1 | 4 |
| 15 | Droplet epitaxy of In/AlGaAs nanostructures on the As-stabilized surface. Journal of Physics: Conference Series, 2018, 1124, 022018. | 0.4 | 2 |
| 16 | Analyticalâ€"Monte Carlo model of the growth of In nanostructures during droplet epitaxy on the triangle-patterned GaAs substrates. Journal of Physics: Conference Series, 2018, 1124, 022001. | 0.4 | 2 |
| 17 | Monte Carlo investigation of the MBE growth of GaAs on the surfaces with different crystallographic orientations. Journal of Physics: Conference Series, 2017, 917, 032034. | 0.4 | 1 |
| 18 | Kinetic Monte Carlo simulation of the indium droplet epitaxy on the Ga-terminated GaAs(001) surface. Journal of Physics: Conference Series, 2017, 917, 032033. | 0.4 | 1 |

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|----|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----------|
| 19 | Formation of nanoscale structures on the surface of gallium arsenide by local anodic oxidation and plasma chemical etching. Journal of Physics: Conference Series, 2018, 1124, 041024. | 0.4 | 1 |
| 20 | Study of the geometrical parameters of In nanostructures during droplet epitaxy on the As-stabilized GaAs(001) surface. Journal of Physics: Conference Series, 2018, 1124, 022025. | 0.4 | 0 |